


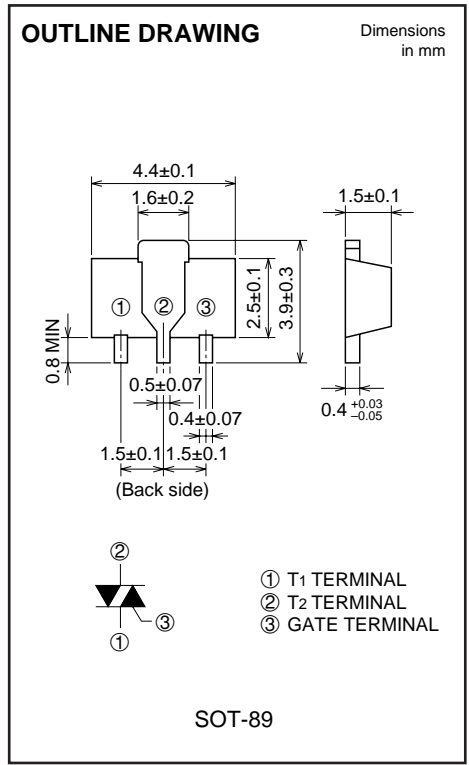
CR08AS

LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

CR08AS



- **IT (AV)** **0.8A**
- **VDRM** **400V/600V**
- **IGT** **100μA**



APPLICATION

Solid state relay, strobe flasher, ignitor, hybrid IC

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8 (marked "AD")	12 (marked "AF")	
VRRM	Repetitive peak reverse voltage	400	600	V
VRSM	Non-repetitive peak reverse voltage	500	720	V
VR (DC)	DC reverse voltage	320	480	V
VDRM	Repetitive peak off-state voltage *1	400	600	V
VD (DC)	DC off-state voltage *1	320	480	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current		1.26	A
IT (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction, Ta=51°C*2	0.8	A
ITSM	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	10	A
I ² _t	I ² _t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	0.42	A ² s
PGM	Peak gate power dissipation		0.5	W
PG (AV)	Average gate power dissipation		0.1	W
VFGM	Peak gate forward voltage		6	V
VRGM	Peak gate reverse voltage		6	V
IFGM	Peak gate forward current		0.3	A
T _j	Junction temperature		-40 ~ +125	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	48	mg

*1. With Gate-to-cathode resistance R_{GK}=1kΩ

CR08AS

LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	$T_j=125^\circ\text{C}$, V_{RRM} applied, $R_{GK}=1\text{k}\Omega$	—	—	0.5	mA
IDRM	Repetitive peak off-state current	$T_j=125^\circ\text{C}$, V_{DRM} applied, $R_{GK}=1\text{k}\Omega$	—	—	0.5	mA
VTM	On-state voltage	$T_a=25^\circ\text{C}$, $I_{TM}=2.5\text{A}$, instantaneous value	—	—	1.5	V
VGT	Gate trigger voltage	$T_a=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$ *4	—	—	0.8	V
VGD	Gate non-trigger voltage	$T_j=125^\circ\text{C}$, $V_D=1/2V_{DRM}$, $R_{GK}=1\text{k}\Omega$	0.2	—	—	V
IGT	Gate trigger current	$T_j=25^\circ\text{C}$, $V_D=6\text{V}$, $I_T=0.1\text{A}$ *4	1	—	100*3	μA
IH	Holding current	$T_j=25^\circ\text{C}$, $V_D=12\text{V}$, $R_{GK}=1\text{k}\Omega$	—	1.5	3	mA
$R_{th(j-a)}$	Thermal resistance	Junction to ambient *2	—	—	65	$^\circ\text{C/W}$

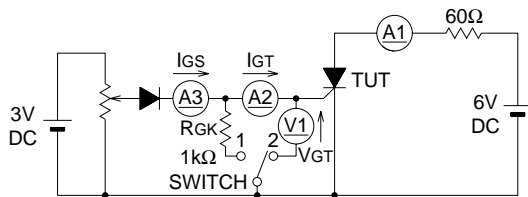
*2. Soldering with ceramic plate (25mm × 25mm × t0.7).

*3. If special values of IGT are required, choose at least two items from those listed in the table below. (Example: AB, BC)

Item	A	B	C
IGT (μA)	1 ~ 30	20 ~ 50	40 ~ 100

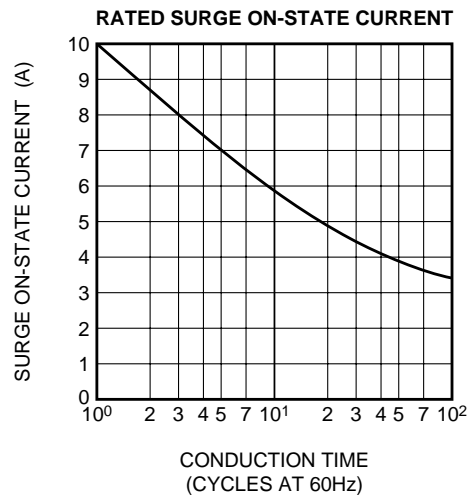
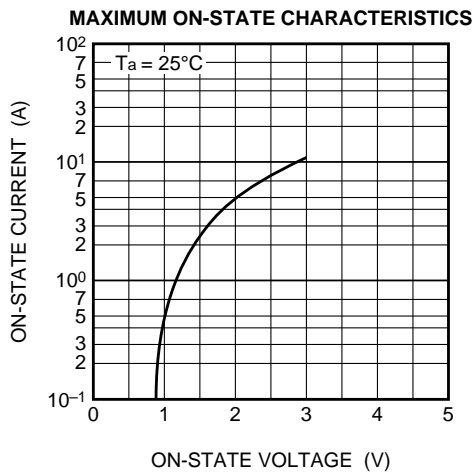
The above values do not include the current flowing through the 1k Ω resistance between the gate and cathode.

*4. IGT, VGT measurement circuit.



SWITCH 1 : IGT measurement
 SWITCH 2 : VGT measurement
 (Inner resistance of voltage meter is about 1k Ω)

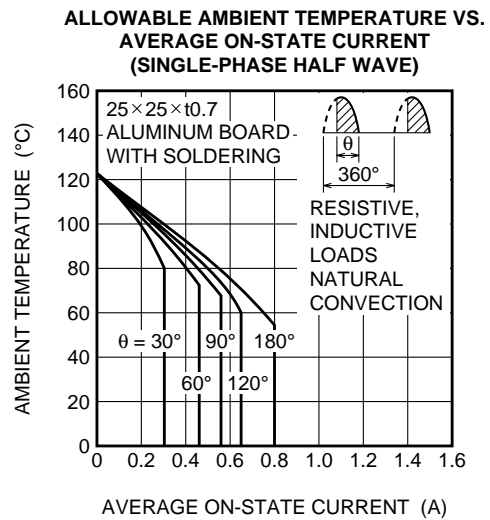
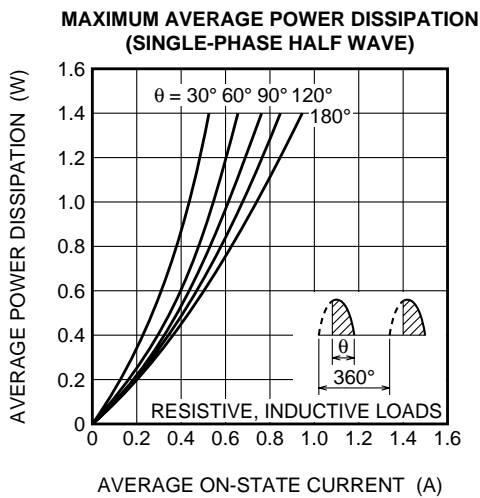
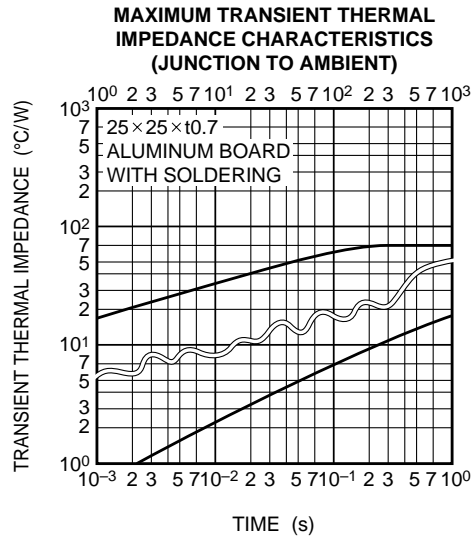
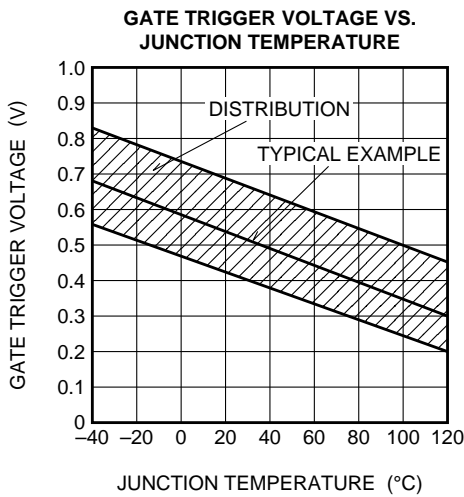
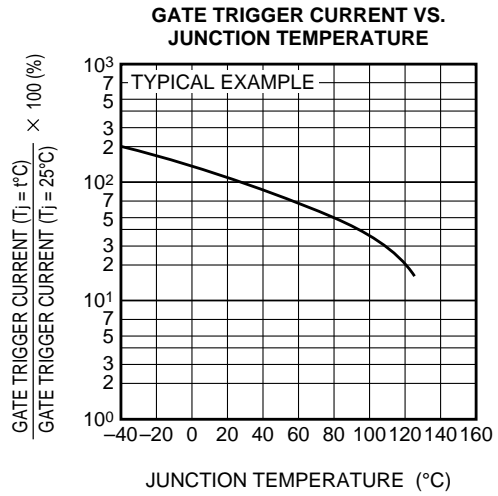
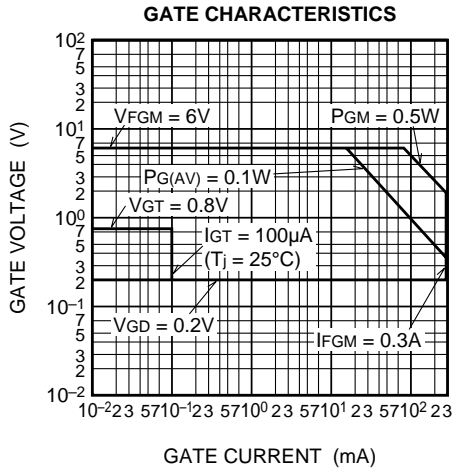
PERFORMANCE CURVES



CR08AS

LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

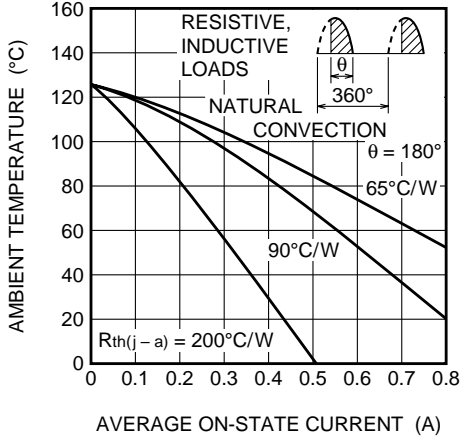


CR08AS

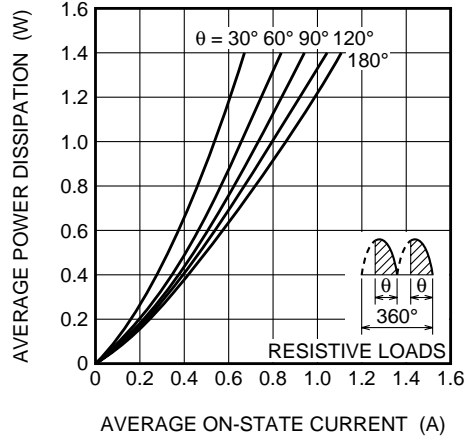
LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

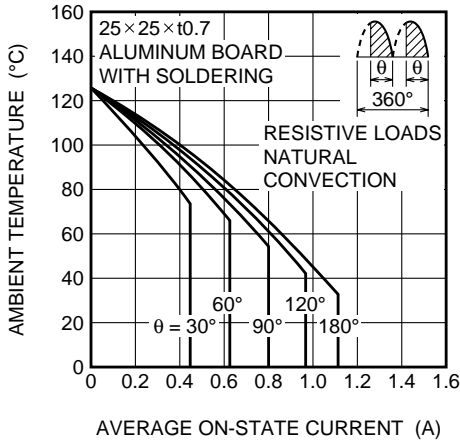
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



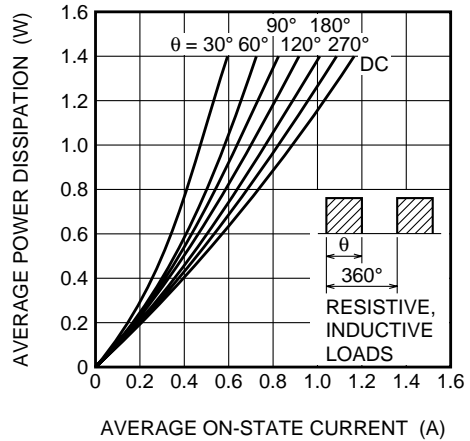
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE FULL WAVE)



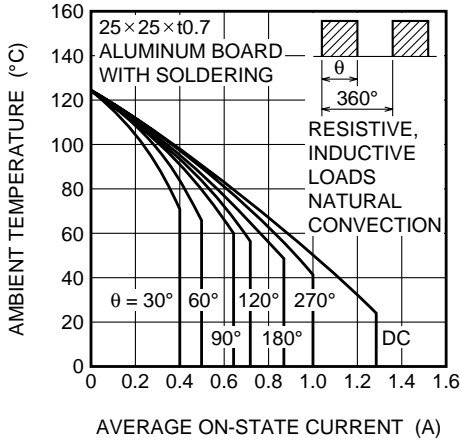
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)



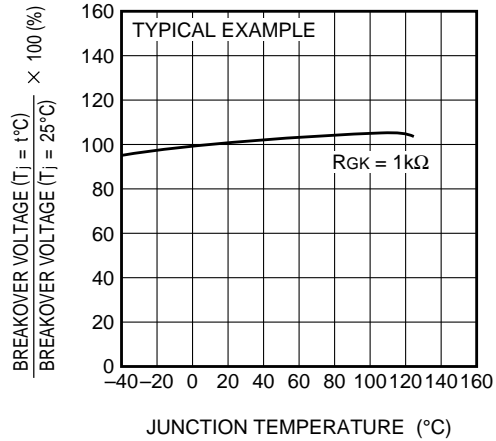
MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



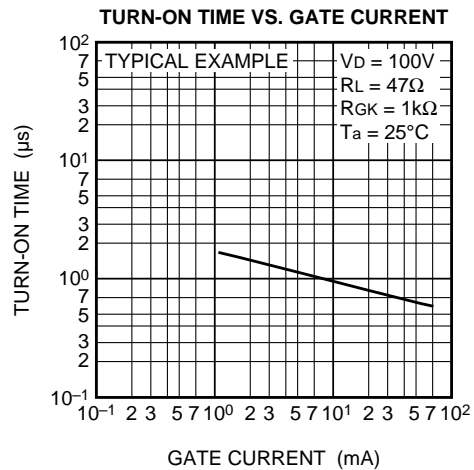
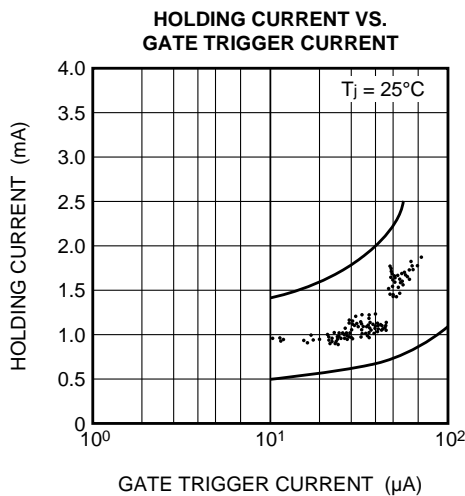
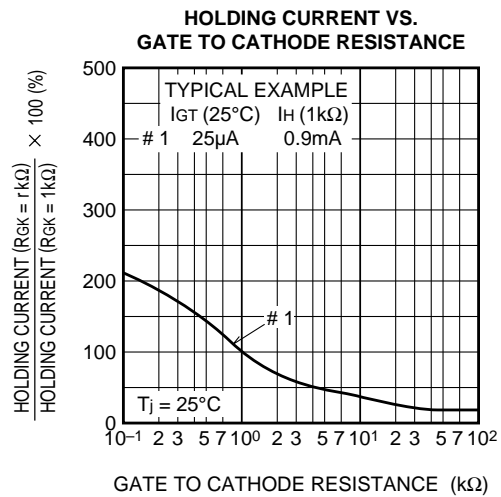
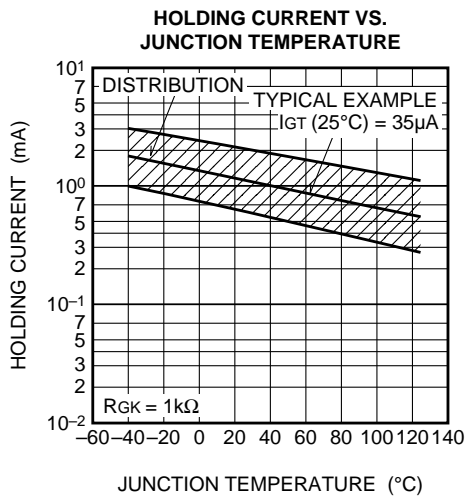
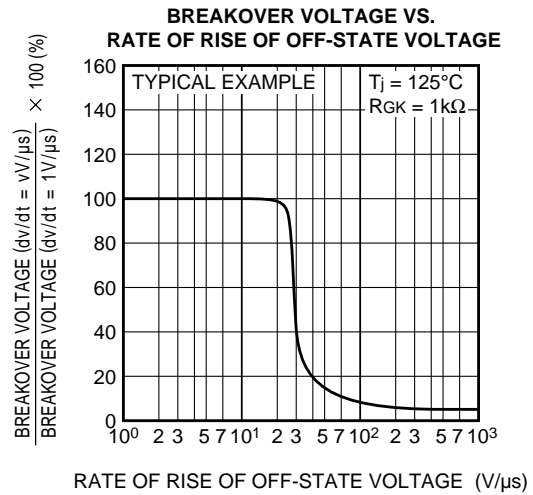
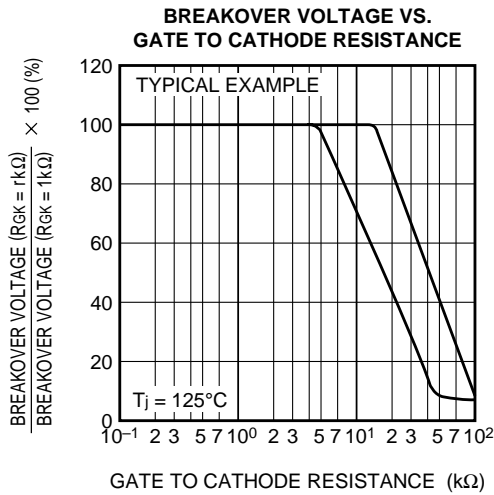
BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



CR08AS

LOW POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE



CR08AS

LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

